16-bit dual supply translating transceiver with configurable voltage translation; 3-state

Rev. 5 — 1 March 2012

Product data sheet

1. General description

The 74AVCH16T245 is a 16-bit transceiver with bidirectional level voltage translation and 3-state outputs. The device can be used as two 8-bit transceivers or as a 16-bit transceiver. It has dual supplies ($V_{CC(A)}$ and $V_{CC(B)}$) for voltage translation and four 8-bit input-output ports (nAn, nBn) each with its own output enable (nOE) and send/receive (nDIR) input for direction control. $V_{CC(A)}$ and $V_{CC(B)}$ can be independently supplied at any voltage between 0.8 V and 3.6 V making the device suitable for low voltage translation between any of the following voltages: 0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V. A HIGH on nDIR selects transmission from nAn to nBn while a LOW on nDIR selects transmission from nBn to nAn. A HIGH on nOE causes the outputs to assume a high-impedance OFF-state

The device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In suspend mode when either $V_{CC(A)}$ or $V_{CC(B)}$ are at GND level, both A and B outputs are in the high-impedance OFF-state. The bus-hold circuitry on the powered-up side always stays active.

The 74AVCH16T245 has active bus hold circuitry which is provided to hold unused or floating data inputs at a valid logic level. This feature eliminates the need for external pull-up or pull-down resistors.

2. Features and benefits

- Wide supply voltage range:
 - ◆ V_{CC(A)}: 0.8 V to 3.6 V
 - V_{CC(B)}: 0.8 V to 3.6 V
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3B exceeds 8000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101D exceeds 1000 V
- Maximum data rates:
 - ◆ 380 Mbit/s (≥ 1.8 V to 3.3 V translation)



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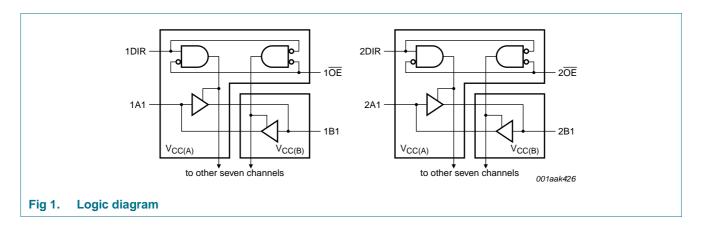
- ◆ 200 Mbit/s (≥ 1.1 V to 3.3 V translation)
- ◆ 200 Mbit/s (≥ 1.1 V to 2.5 V translation)
- 200 Mbit/s (\geq 1.1 V to 1.8 V translation)
- 150 Mbit/s (\geq 1.1 V to 1.5 V translation)
- ◆ 100 Mbit/s (≥ 1.1 V to 1.2 V translation)
- Suspend mode
- Bus hold on data inputs
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C

3. Ordering information

Ordering information Table 1. Package Type number Temperature range Name Description Version 74AVCH16T245DGG -40 °C to +125 °C TSSOP48 plastic thin shrink small outline package; 48 leads; SOT362-1 body width 6.1 mm 74AVCH16T245DGV -40 °C to +125 °C TSSOP48^[1] plastic thin shrink small outline package; 48 leads; SOT480-1 body width 4.4 mm; lead pitch 0.4 mm 74AVCH16T245EV -40 °C to +125 °C VFBGA56 plastic very thin fine-pitch ball grid array package; SOT702-1 56 balls; body $4.5 \times 7 \times 0.65$ mm 74AVCH16T245BX -40 °C to +125 °C HXQFN60 plastic compatible thermal enhanced extremely SOT1134-2 thin guad flat package; no leads; 60 terminals; body $4 \times 6 \times 0.5$ mm

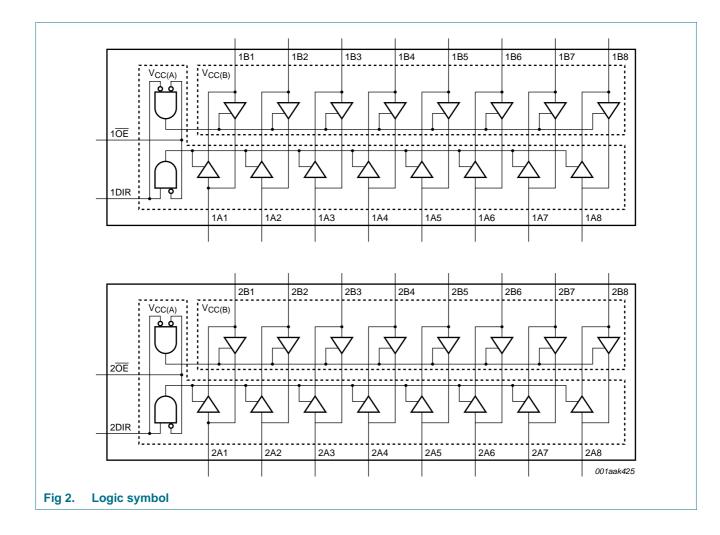
[1] Also known as TVSOP48.

4. Functional diagram



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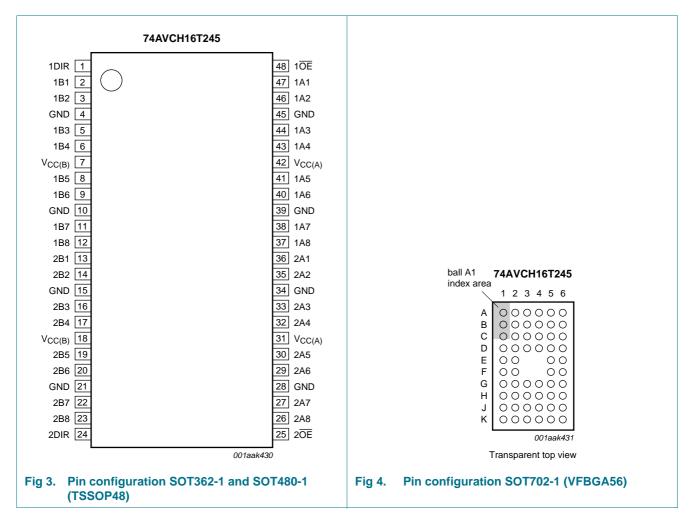
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5. Pinning information

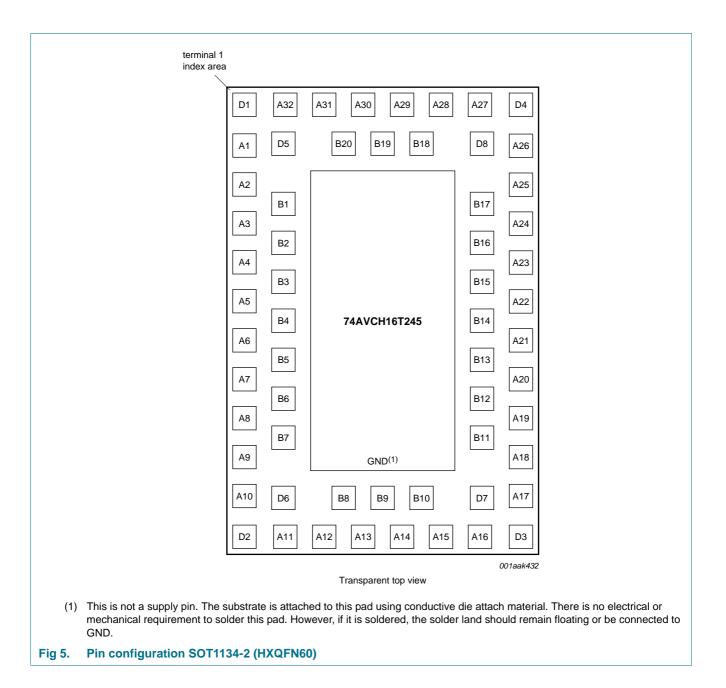
5.1 Pinning



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5.2 Pin description

Symbol	Pin			Description
	SOT362-1 and SOT480-1	SOT702-1	SOT1134-2	-
1DIR, 2DIR	1, 24	A1, K1	A30, A13	direction control
1B1 to 1B8	2, 3, 5, 6, 8, 9, 11, 12	B2, B1, C2, C1, D2, D1, E2, E1	B20, A31, D5, D1, A2, B2, B3, A5	data input or output
2B1 to 2B8	13, 14, 16, 17, 19, 20, 22, 23	F1, F2, G1, G2, H1, H2, J1, J2	A6, B5, B6, A9, D2, D6, A12, B8	data input or output
GND ^[1]	4, 10, 15, 21, 28, 34, 39, 45	B3, D3, G3, J3, J4, G4, D4, B4	A32, A3, A8, A11, A16, A19, A24, A27	ground (0 V)
V _{CC(B)}	7, 18	C3, H3	A1, A10	supply voltage B (nBn inputs are referenced to $V_{CC(B)}$)
1 <u>0E</u> , 2 <u>0E</u>	48, 25	A6, K6	A29, A14	output enable input (active LOW)
1A1 to 1A8	47, 46, 44, 43, 41, 40, 38, 37	B5, B6, C5, C6, D5, D6, E5, E6	B18, A28, D8, D4, A25, B16, B15, A22	data input or output
2A1 to 2A8	36, 35, 33, 32, 30, 29, 27, 26	F6, F5, G6, G5, H6, H5, J6, J5	A21, B13, B12, A18, D3, D7, A15, B10	data input or output
V _{CC(A)}	31, 42	C4, H4	A17, A26	supply voltage A (nAn, n $\overline{\text{OE}}$ and nDIR inputs are referenced to $V_{CC(A)}$
n.c.	-	A2, A3, A4, A5, K2, K3, K4, K5	A4, A7, A20, A23, B1, B4, B7, B9, B11, B14, B17, B19	not connected

[1] All GND pins must be connected to ground (0 V).

6. Functional description

Table 3. Function table^[1]

Supply voltage	Input		Input/output ^[3]	
V _{CC(A)} , V _{CC(B)}	nOE ^[2]	nDIR ^[2]	nAn ^[2]	nBn ^[2]
0.8 V to 3.6 V	L	L	nAn = nBn	input
0.8 V to 3.6 V	L	Н	input	nBn = nAn
0.8 V to 3.6 V	Н	Х	Z	Z
GND ^[3]	Х	Х	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] The nAn, nDIR and n \overline{OE} input circuit is referenced to V_{CC(A)}; The nBn input circuit is referenced to V_{CC(B)}.

[3] If at least one of $V_{CC(A)}$ or $V_{CC(B)}$ is at GND level, the device goes into suspend mode.

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

			•		,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		-0.5	+4.6	V
V _{CC(B)}	supply voltage B		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode	<u>[1][2][3]</u> –0.5	V _{CCO} + 0.5	V
		Suspend or 3-state mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	[2] _	±50	mA
I _{CC}	supply current	I _{CC(A)} or I _{CC(B)}	-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$;			
		TSSOP48 package	<u>[4]</u> _	500	mW
		VFBGA56 package	<u>[5]</u> _	1000	mW
		HXQFN60 package	<u>[5]</u> _	1000	mW

[1] The minimum input voltage ratings and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] V_{CCO} is the supply voltage associated with the output port.

[3] V_{CCO} + 0.5 V should not exceed 4.6 V.

[4] Above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

[5] Above 70 °C the value of P_{tot} derates linearly with 1.8 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		0.8	3.6	V
V _{CC(B)}	supply voltage B		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	[1] 0	V _{cco}	V
		Suspend or 3-state mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CCI} = 0.8 \text{ V}$ to 3.6 V	[2] -	5	ns/V

[1] V_{CCO} is the supply voltage associated with the output port.

[2] V_{CCI} is the supply voltage associated with the input port.

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9. Static characteristics

Table 6. Typical static characteristics at $T_{amb} = 25 \text{ °C}[1][2]$

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O} = -1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.69	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 1.5 mA; $V_{CC(A)}$ = $V_{CC(B)}$ = 0.8 V	-	0.07	-	V
lı	input leakage current	nDIR, n \overline{OE} input; V _I = 0 V or 3.6 V; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V	-	±0.025	±0.25	μA
I _{BHL}	bus hold LOW current	A or B port; $V_I = 0.42$ V; $V_{CC(A)} = V_{CC(B)} = 1.2$ V	<u>[3]</u>	26	-	μΑ
I _{BHH}	bus hold HIGH current	A or B port; $V_I = 0.78$ V; $V_{CC(A)} = V_{CC(B)} = 1.2$ V	<u>[4]</u> _	-24	-	μΑ
I _{BHLO}	bus hold LOW overdrive current	A or B port; $V_{CC(A)} = V_{CC(B)} = 1.2 V$	<u>[5]</u> _	27	-	μΑ
I _{BHHO}	bus hold HIGH overdrive current	A or B port; $V_{CC(A)} = V_{CC(B)} = 1.2 \text{ V}$	<u>[6]</u> _	-26	-	μA
I _{OZ}	OFF-state output current	A or B port; $V_O = 0 V$ or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 3.6 V$	[7] -	±0.5	±2.5	μA
		suspend mode A port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = 3.6$ V; $V_{CC(B)} = 0$ V	[7] -	±0.5	±2.5	μΑ
		suspend mode B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 3.6$ V	[7] _	±0.5	±2.5	μA
I _{OFF}	power-off leakage current	A port; V ₁ or V ₀ = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0.8 V to 3.6 V	-	±0.1	±1	μA
		B port; V _I or V _O = 0 V to 3.6 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0.8 V to 3.6 V	-	±0.1	±1	μΑ
CI	input capacitance	nDIR, n \overline{OE} input; V _I = 0 V or 3.3 V; V _{CC(A)} = V _{CC(B)} = 3.3 V	-	2.0	-	pF
C _{I/O}	input/output capacitance	A and B port; $V_O = 3.3 \text{ V or } 0 \text{ V}$; $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$	-	4.5	-	pF

[1] V_{CCO} is the supply voltage associated with the output port.

[2] V_{CCI} is the supply voltage associated with the data input port.

[3] The bus hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_I to GND and then raising it to V_{IL} max.

[4] The bus hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_I to V_{CC} and then lowering it to V_{IH} min.

[5] An external driver must source at least I_{BHLO} to switch this node from LOW to HIGH.

[6] An external driver must sink at least I_{BHHO} to switch this node from HIGH to LOW.

[7] For I/O ports, the parameter I_{OZ} includes the input leakage current.

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Table 7. Static characteristics [1][2]

Symbol	Parameter	Conditions	–40 °C t	o +85 °C	–40 °C to	• +125 °C	Uni
			Min	Max	Min	Max	
/ _{IH}	HIGH-level	data input					
	input voltage	V _{CCI} = 0.8 V	0.70V _{CCI}	-	0.70V _{CCI}	-	V
		V _{CCI} = 1.1 V to 1.95 V	$0.65V_{CCI}$	-	0.65V _{CCI}	-	V
		V _{CCI} = 2.3 V to 2.7 V	1.6	-	1.6	-	V
		V _{CCI} = 3.0 V to 3.6 V	2	-	2	-	V
		nDIR, nOE input					
		$V_{CC(A)} = 0.8 V$	0.70V _{CC(A)}	-	0.70V _{CC(A)}	-	V
		V _{CC(A)} = 1.1 V to 1.95 V	0.65V _{CC(A)}	-	0.65V _{CC(A)}	-	V
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	1.6	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	2	-	2	-	V
′ _{IL}	LOW-level	data input					
	input voltage	V _{CCI} = 0.8 V	-	0.30V _{CCI}	-	0.30V _{CCI}	V
		V _{CCI} = 1.1 V to 1.95 V	-	0.35V _{CCI}	-	0.35V _{CCI}	V
		V _{CCI} = 2.3 V to 2.7 V	-	0.7	-	0.7	V
		V _{CCI} = 3.0 V to 3.6 V	-	0.8	-	0.8	V
		nDIR, nOE input					
		$V_{CC(A)} = 0.8 V$	-	0.30V _{CC(A)}	-	0.30V _{CC(A)}	V
		V _{CC(A)} = 1.1 V to 1.95 V	-	0.35V _{CC(A)}	-	0.35V _{CC(A)}	V
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	-	0.7	-	0.7	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	-	0.8	-	0.8	V
он	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$					
	output voltage	$I_{O} = -100 \ \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \ V \text{ to } 3.6 \ V$	V _{CCO} – 0.1	-	$V_{CCO}-0.1$	-	V
		$I_{O} = -3 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	0.85	-	0.85	-	V
		$I_{O} = -6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	1.05	-	1.05	-	V
		$I_{O} = -8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	1.2	-	1.2	-	V
		$I_{O} = -9 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	1.75	-	1.75	-	V
		$I_{O} = -12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3	-	2.3	-	V
OL	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$					
	output voltage	$I_{O} = 100 \ \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \ V \text{ to } 3.6 \ V$	-	0.1	-	0.1	V
		$I_{O} = 3 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	-	0.25	-	0.25	V
		$I_{O} = 6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	-	0.35	-	0.35	V
		$I_{O} = 8 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	-	0.45	-	0.45	V
		$I_{O} = 9 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	-	0.55	-	0.55	V
		$I_{O} = 12 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	-	0.7	-	0.7	V
	input leakage current	nDIR, n \overline{OE} input; V _I = 0 V or 3.6 V; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V	-	±1	-	±5	μA

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Symbol	Parameter	Conditions		–40 °C t	o +85 °C	-40 °C to	• +125 °C	Unit
				Min	Max	Min	Max	
I _{BHL}	bus hold	A or B port	[3]					
	LOW current	$V_{I} = 0.49 \text{ V}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$		15	-	15	-	μΑ
		$V_{I} = 0.58 V;$ $V_{CC(A)} = V_{CC(B)} = 1.65 V$		25	-	25	-	μA
		$V_{I} = 0.70 \text{ V}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$		45	-	45	-	μΑ
		$V_{I} = 0.80 \text{ V}; V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$		100	-	90	-	μΑ
І _{внн}	bus hold	A or B port	[4]					
	HIGH current	$V_{I} = 0.91 \text{ V}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$		-15	-	-15	-	μA
		$V_{I} = 1.07 \text{ V};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$		-25	-	-25	-	μΑ
		$V_{I} = 1.60 \text{ V}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$		-45	-	-45	-	μΑ
		$V_{I} = 2.00 \text{ V}; V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$		-100	-	-100	-	μΑ
I _{BHLO}	bus hold	A or B port	[5]					
	LOW overdrive	$V_{CC(A)} = V_{CC(B)} = 1.6 \text{ V}$		125	-	125	-	μΑ
	current	$V_{CC(A)} = V_{CC(B)} = 1.95 V$		200	-	200	-	μΑ
		$V_{CC(A)} = V_{CC(B)} = 2.7 \text{ V}$		300	-	300	-	μΑ
		$V_{CC(A)} = V_{CC(B)} = 3.6 \text{ V}$		500	-	500	-	μΑ
І _{внно}	bus hold	A or B port	[6]					
	HIGH overdrive	$V_{CC(A)} = V_{CC(B)} = 1.6 \text{ V}$		-125	-	-125	-	μΑ
	current	$V_{CC(A)} = V_{CC(B)} = 1.95 V$		-200	-	-200	-	μΑ
		$V_{CC(A)} = V_{CC(B)} = 2.7 \text{ V}$		-300	-	-300	-	μΑ
		$V_{CC(A)} = V_{CC(B)} = 3.6 \text{ V}$		-500	-	-500	-	μΑ
l _{oz}	OFF-state output	A or B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 3.6$ V	[7]	-	±5	-	±30	μΑ
	current	suspend mode A port; $V_O = 0 V \text{ or } V_{CCO}; V_{CC(A)} = 3.6 V;$ $V_{CC(B)} = 0 V$	[7]	-	±5	-	±30	μA
		suspend mode B port; $V_O = 0 V \text{ or } V_{CCO}; V_{CC(A)} = 0 V;$ $V_{CC(B)} = 3.6 V$	[7]	-	±5	-	±30	μA
I _{OFF}	power-off leakage	A port; V ₁ or V ₀ = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0.8 V to 3.6 V		-	±5	-	±30	μΑ
	current	B port; V ₁ or V ₀ = 0 V to 3.6 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0.8 V to 3.6 V		-	±5	-	±30	μΑ

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

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Symbol	Parameter	Conditions	–40 °C t	o +85 °C	–40 °C to	o +125 ℃	Unit
			Min	Max	Min	Max	
I _{CC}	supply	A port; $V_I = 0$ V or V_{CCI} ; $I_O = 0$ A			1		l
	current	$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	30	-	125	μA
		$V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	25	-	100	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	25	-	100	μΑ
		$V_{CC(A)} = 0 V; V_{CC(B)} = 3.6 V$	-5	-	-20	-	μA
		B port; $V_I = 0 V$ or V_{CCI} ; $I_O = 0 A$					
			$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	30	-	125
		$V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	25	-	100	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-5	-	-20	-	μΑ
		$V_{CC(A)} = 0 V; V_{CC(B)} = 3.6 V$	-	25	-	100	μA
		A plus B port $(I_{CC(A)} + I_{CC(B)});$ $I_O = 0 A; V_I = 0 V \text{ or } V_{CCI};$ $V_{CC(A)} = 0.8 V \text{ to } 3.6 V;$ $V_{CC(B)} = 0.8 V \text{ to } 3.6 V$	-	55	-	185	μΑ
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0$ A; $V_I = 0$ V or V_{CCI} ; $V_{CC(A)} = 1.1$ V to 3.6 V; $V_{CC(B)} = 1.1$ V to 3.6 V	-	45	-	150	μΑ

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

[1] V_{CCO} is the supply voltage associated with the output port.

[2] V_{CCI} is the supply voltage associated with the data input port.

- [3] The bus hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_I to GND and then raising it to V_{IL} max.
- [4] The bus hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_I to V_{CC} and then lowering it to V_{IH} min.
- [5] An external driver must source at least I_{BHLO} to switch this node from LOW to HIGH.
- [6] An external driver must sink at least I_{BHHO} to switch this node from HIGH to LOW.
- [7] For I/O ports, the parameter I_{OZ} includes the input leakage current.

Table 8. Typical total supply current (I_{CC(A)} + I_{CC(B)})

V _{CC(A)}	V _{CC(B)}	V _{CC(B)}								
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V			
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μA		
0.8 V	0.1	0.1	0.1	0.1	0.1	0.3	1.6	μA		
1.2 V	0.1	0.1	0.1	0.1	0.1	0.1	0.8	μA		
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.4	μA		
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.2	μA		
2.5 V	0.1	0.3	0.1	0.1	0.1	0.1	0.1	μA		
3.3 V	0.1	1.6	0.8	0.4	0.2	0.1	0.1	μA		

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10. Dynamic characteristics

Table 9. Typical power dissipation capacitance at $V_{CC(A)} = V_{CC(B)}$ and $T_{amb} = 25 \text{ °C } [1][2]$

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions			V _{CC(A)} =	= V _{CC(B)}			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C _{PD}	power dissipation capacitance	A port: (direction nAn to nBn); output enabled	0.2	0.2	0.2	0.2	0.3	0.4	рF
		A port: (direction nAn to nBn); output disabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		A port: (direction nBn to nAn); output enabled	9	9.7	9.8	10.3	11.7	13.7	pF
		A port: (direction nBn to nAn); output disabled	0.6	0.6	0.6	0.7	0.7	0.7	pF
		B port: (direction nAn to nBn); output enabled	9	9.7	9.8	10.3	11.7	13.7	pF
		B port: (direction nAn to nBn); output disabled	0.6	0.6	0.6	0.7	0.7	0.7	pF
		B port: (direction nBn to nAn); output enabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		B port: (direction nBn to nAn); output disabled	0.2	0.2	0.2	0.2	0.3	0.4	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

[2] $f_i = 10 \text{ MHz}$; $V_I = \text{GND}$ to V_{CC} ; $t_r = t_f = 1 \text{ ns}$; $C_L = 0 \text{ pF}$; $R_L = \infty \Omega$.

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Symbol	Parameter	Conditions	V _{CC(B)}						
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t _{pd}	propagation delay	nAn to nBn	14.4	7.0	6.2	6.0	5.9	6.0	ns
		nBn to nAn	14.4	12.4	12.1	11.9	11.8	11.8	ns
t _{dis}	disable time	nOE to nAn	16.2	16.2	16.2	16.2	16.2	16.2	ns
		nOE to nBn	17.6	10.0	9.0	9.1	8.7	9.3	ns
t _{en}	enable time	nOE to nAn	21.9	21.9	21.9	21.9	21.9	21.9	ns
		nOE to nBn	22.2	11.1	9.8	9.4	9.4	9.6	ns

Table 10. Typical dynamic characteristics at $V_{CC(A)} = 0.8 V$ and $T_{amb} = 25 \ ^{\circ}C \ ^{(1)}$ Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8; for wave forms see Figure 6 and Figure 7

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

Table 11. Typical dynamic characteristics at $V_{CC(B)} = 0.8$ V and $T_{amb} = 25$ °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8; for wave forms see Figure 6 and Figure 7

Symbol	Parameter	Conditions	V _{CC(A)}						Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t _{pd}	propagation delay	nAn to nBn	14.4	12.4	12.1	11.9	11.8	11.8	ns
		nBn to nAn	14.4	7.0	6.2	6.0	5.9	6.0	ns
t _{dis}	disable time	nOE to nAn	16.2	5.9	4.4	4.2	3.1	3.5	ns
		nOE to nBn	17.6	14.2	13.7	13.6	13.3	13.1	ns
t _{en}	enable time	nOE to nAn	21.9	6.4	4.4	3.5	2.6	2.3	ns
		nOE to nBn	22.2	17.7	17.2	17.0	16.8	16.7	ns

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

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Symbol	Parameter	Conditions	V _{CC(B)}								Un		
			$1.2 V \pm 0.1 V$		1.5 V :	± 0.1 V	1.8 V ± 0.15 V		$2.5~V\pm0.2~V$		$3.3~V\pm0.3~V$		
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	-
$V_{CC(A)} =$	1.1 V to 1.3 V												
t _{pd}	propagation	nAn to nBn	0.5	9.2	0.5	6.9	0.5	6.0	0.5	5.1	0.5	4.9	ns
delay	nBn to nAn	0.5	9.2	0.5	8.7	0.5	8.5	0.5	8.2	0.5	8.0	ns	
t _{dis}	disable time	nOE to nAn	1.5	11.6	1.5	11.6	1.5	11.6	1.5	11.6	1.5	11.6	ns
		nOE to nBn	1.5	12.5	1.5	9.7	1.5	9.5	1.0	8.1	1.0	8.9	ns
t _{en}	enable time	n <mark>OE</mark> to nAn	1.0	14.5	1.0	14.5	1.0	14.5	1.0	14.5	1.0	14.5	ns
		nOE to nBn	1.1	14.9	1.1	11.0	1.1	9.6	1.0	8.1	1.0	7.7	ns
$V_{CC(A)} =$	1.4 V to 1.6 V												
t _{pd}	propagation	nAn to nBn	0.5	8.7	0.5	6.2	0.5	5.2	0.5	4.1	0.5	3.7	ns
	delay	nBn to nAn	0.5	6.9	0.5	6.2	0.5	5.9	0.5	5.6	0.5	5.5	ns
t _{dis}	disable time	nOE to nAn	1.5	9.1	1.5	9.1	1.5	9.1	1.5	9.1	1.5	9.1	ns
		nOE to nBn	1.5	11.4	1.5	8.7	1.5	7.5	1.0	6.5	1.0	6.3	ns
t _{en}	enable time	nOE to nAn	1.0	10.1	1.0	10.1	1.0	10.1	1.0	10.1	1.0	10.1	ns
		nOE to nBn	1.0	13.5	1.0	10.1	0.5	8.1	0.5	5.9	0.5	5.2	ns
$V_{CC(A)} =$	1.65 V to 1.95	V											
t _{pd}	propagation	nAn to nBn	0.5	8.5	0.5	5.9	0.5	4.8	0.5	3.7	0.5	3.3	ns
delay	nBn to nAn	0.5	6.0	0.5	5.2	0.5	4.8	0.5	4.5	0.5	4.4	ns	
t _{dis}	disable time	n <mark>OE</mark> to nAn	1.5	7.7	1.5	7.7	1.5	7.7	1.5	7.7	1.5	7.7	ns
		nOE to nBn	1.5	11.1	1.5	8.4	1.5	7.1	1.0	5.9	1.0	5.7	ns
t _{en}	enable time	n <mark>OE</mark> to nAn	1.0	7.8	1.0	7.8	1.0	7.8	1.0	7.8	1.0	7.8	ns
		nOE to nBn	1.0	13.0	1.0	9.2	0.5	7.4	0.5	5.3	0.5	4.5	ns
V _{CC(A)} =	2.3 V to 2.7 V												
t _{pd}	propagation	nAn to nBn	0.5	8.2	0.5	5.6	0.5	4.6	0.5	3.3	0.5	2.8	ns
	delay	nBn to nAn	0.5	5.1	0.5	4.1	0.5	3.7	0.5	3.4	0.5	3.2	ns
t _{dis}	disable time	n <mark>OE</mark> to nAn	1.0	6.1	1.0	6.1	1.0	6.1	1.0	6.1	1.0	6.1	ns
		nOE to nBn	1.0	10.6	1.0	7.9	1.0	6.6	1.0	6.1	1.0	5.2	ns
t _{en}	enable time	n <mark>OE</mark> to nAn	0.5	5.3	0.5	5.3	0.5	5.3	0.5	5.3	0.5	5.3	ns
		nOE to nBn	0.5	12.5	0.5	9.4	0.5	7.3	0.5	5.1	0.5	4.5	ns
V _{CC(A)} =	3.0 V to 3.6 V												
t _{pd}	propagation	nAn to nBn	0.5	8.0	0.5	5.5	0.5	4.4	0.5	3.2	0.5	2.7	ns
	delay	nBn to nAn	0.5	4.9	0.5	3.7	0.5	3.3	0.5	2.9	0.5	2.7	ns
t _{dis}	disable time	nOE to nAn	0.5	5.0	0.5	5.0	0.5	5.0	0.5	5.0	0.5	5.0	ns
		nOE to nBn	1.0	10.3	1.0	7.7	1.0	6.5	1.0	5.2	0.5	5.0	ns
t _{en}	enable time	nOE to nAn	0.5	4.3	0.5	4.3	0.5	4.2	0.5	4.1	0.5	4.0	ns
		nOE to nBn	0.5	12.4	0.5	9.3	0.5	7.2	0.5	4.9	0.5	4.0	ns

Table 12. Dynamic characteristics for temperature range $-40 \,^{\circ}$ C to $+85 \,^{\circ}$ C [1] Voltages are referenced to GND (ground $= 0 \,^{\circ}$ V); for test circuit see Figure 8; for wave forms see Figure 6 and Figure 7

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

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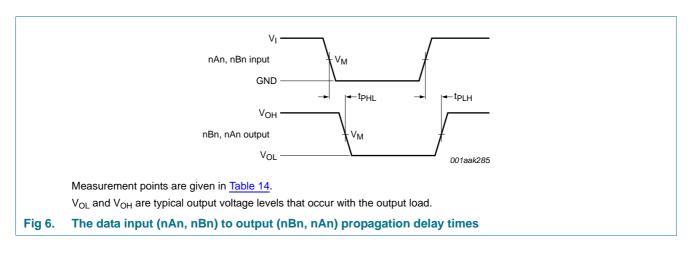
Symbol	Parameter	Conditions	V _{CC(B)}								Uni		
			$1.2 V \pm 0.1 V$		$1.5 V \pm 0.1 V$		1.8 V ± 0.15 V		$2.5~V\pm0.2~V$		$3.3 V \pm 0.3 V$		
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	-
V _{CC(A)} =	1.1 V to 1.3 V	'											
t _{pd}	propagation	nAn to nBn	0.5	10.2	0.5	7.6	0.5	6.6	0.5	5.7	0.5	5.4	ns
	delay	nBn to nAn	0.5	10.2	0.5	9.6	0.5	9.4	0.5	9.1	0.5	8.8	ns
t _{dis}	disable time	nOE to nAn	1.5	12.8	1.5	12.8	1.5	12.8	1.5	12.8	1.5	12.8	ns
		nOE to nBn	1.5	13.8	1.5	10.7	1.5	10.5	1.0	9.0	1.5	9.8	ns
t _{en}	enable time	nOE to nAn	1.0	16.0	1.0	16.0	1.0	16.0	1.0	16.0	1.0	16.0	ns
		nOE to nBn	1.1	16.4	1.1	12.1	1.1	10.6	1.0	9.0	1.0	8.5	ns
V _{CC(A)} =	1.4 V to 1.6 V												
t _{pd}	propagation	nAn to nBn	0.5	9.6	0.5	6.9	0.5	5.8	0.5	4.6	0.5	4.1	ns
	delay	nBn to nAn	0.5	7.6	0.5	6.9	0.5	6.5	0.5	6.2	0.5	6.1	ns
t _{dis}	disable time	nOE to nAn	1.5	10.1	1.5	10.1	1.5	10.1	1.5	10.1	1.5	10.1	ns
		nOE to nBn	1.5	12.6	1.5	9.6	1.5	8.3	1.0	7.2	1.0	7.0	ns
t _{en}	enable time	nOE to nAn	1.0	11.2	1.0	11.2	1.0	11.2	1.0	11.2	1.0	11.2	ns
		nOE to nBn	1.0	14.9	1.0	11.2	0.5	9.0	0.5	6.5	0.5	5.8	ns
V _{CC(A)} =	1.65 V to 1.95	V											
t _{pd} propaga delay	propagation	nAn to nBn	0.5	9.4	0.5	6.5	0.5	5.3	0.5	4.1	0.5	3.7	ns
	delay	nBn to nAn	0.5	6.6	0.5	5.8	0.5	5.3	0.5	5.0	0.5	4.9	ns
t _{dis}	disable time	n <mark>OE</mark> to nAn	1.5	8.5	1.5	8.5	1.5	8.5	1.5	8.5	1.5	8.5	ns
		nOE to nBn	1.5	12.3	1.5	9.3	1.5	7.9	1.0	6.5	1.0	6.3	ns
t _{en}	enable time	n <mark>OE</mark> to nAn	1.0	8.6	1.0	8.6	1.0	8.6	1.0	8.6	1.0	8.6	ns
		nOE to nBn	1.0	14.3	1.0	10.2	0.5	8.2	0.5	5.9	0.5	5.0	ns
V _{CC(A)} =	2.3 V to 2.7 V												
t _{pd}	propagation	nAn to nBn	0.5	9.1	0.5	6.2	0.5	5.1	0.5	3.7	0.5	3.1	ns
	delay	nBn to nAn	0.5	5.7	0.5	4.6	0.5	4.1	0.5	3.8	0.5	3.6	ns
t _{dis}	disable time	n <mark>OE</mark> to nAn	1.0	6.8	1.0	6.8	1.0	6.8	1.0	6.8	1.0	6.8	ns
		nOE to nBn	1.0	11.7	1.0	8.7	1.0	7.3	1.0	6.8	1.0	5.8	ns
t _{en}	enable time	nOE to nAn	0.5	5.9	0.5	5.9	0.5	5.9	0.5	5.9	0.5	5.9	ns
		nOE to nBn	0.5	13.8	0.5	10.4	0.5	8.1	0.5	5.7	0.5	5.0	ns
$V_{CC(A)} =$	3.0 V to 3.6 V												
t _{pd}	propagation	nAn to nBn	0.5	8.8	0.5	6.1	0.5	4.9	0.5	3.6	0.5	3.0	ns
	delay	nBn to nAn	0.5	5.4	0.5	4.1	0.5	3.7	0.5	3.2	0.5	3.0	ns
t _{dis}	disable time	nOE to nAn	0.5	5.5	0.5	5.5	0.5	5.5	0.5	5.5	0.5	5.5	ns
-		nOE to nBn	1.0	11.4	1.0	8.5	1.0	7.2	1.0	5.8	0.5	5.5	ns
t _{en}	enable time	nOE to nAn	0.5	4.8	0.5	4.8	0.5	4.7	0.5	4.6	0.5	4.4	ns
•en		nOE to nBn	0.5	13.7	0.5	10.3	0.5	8.0	0.5	5.4	0.5	4.4	ns

Table 13. Dynamic characteristics for temperature range $-40 \text{ °C to } +125 \text{ °C } \stackrel{[1]}{\longrightarrow}$

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

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11. Waveforms



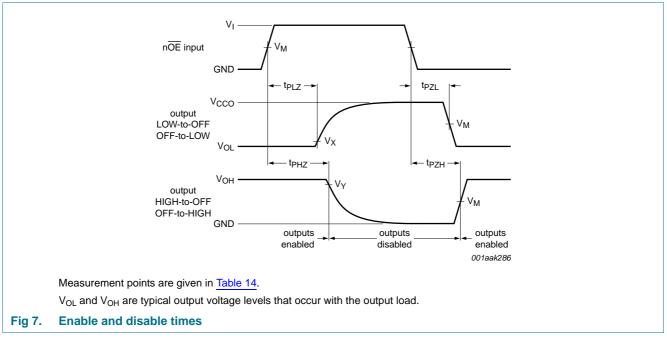


Table 14.Measurement points

Supply voltage	Input ^[1]	Output ^[2]		
V _{CC(A)} , V _{CC(B)}	V _M	V _M	V _X	V _Y
0.8 V to 1.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} – 0.1 V
1.65 V to 2.7 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V
3.0 V to 3.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} – 0.3 V

[1] V_{CCI} is the supply voltage associated with the data input port.

[2] V_{CCO} is the supply voltage associated with the output port.

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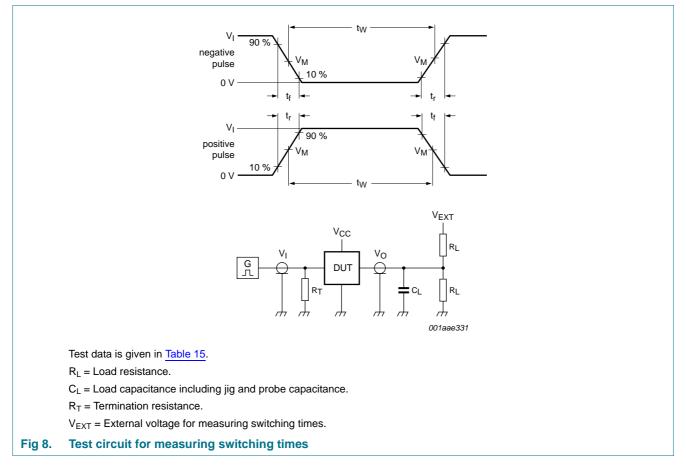


Table 15. Test data

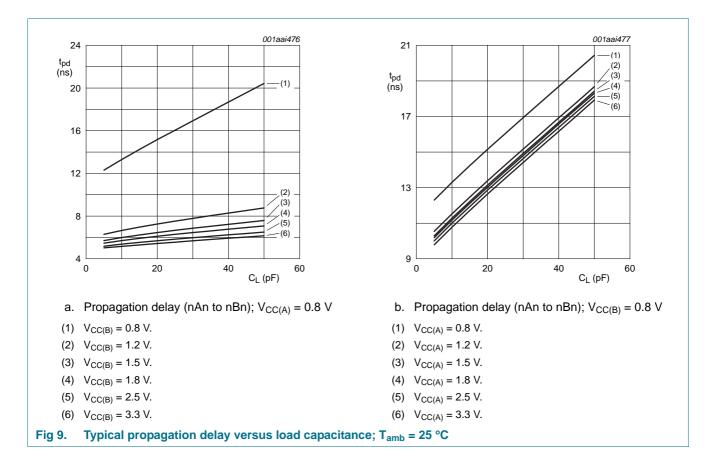
Supply voltage	Input		Load	Load		V _{EXT}		
$V_{CC(A)}, V_{CC(B)}$	V <mark>[^{1]}</mark>	∆t/∆V[2]	CL	RL	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} [3]	
0.8 V to 1.6 V	V _{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	
1.65 V to 2.7 V	V _{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	
3.0 V to 3.6 V	V _{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	

[1] V_{CCI} is the supply voltage associated with the data input port.

 $[2] \quad dV/dt \geq 1.0 \ V/ns$

[3] V_{CCO} is the supply voltage associated with the output port.

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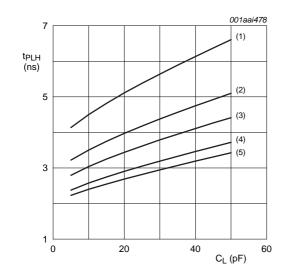


12. Typical propagation delay characteristics

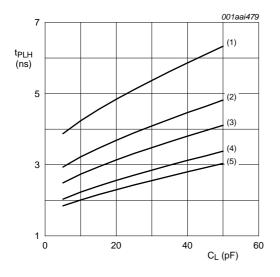
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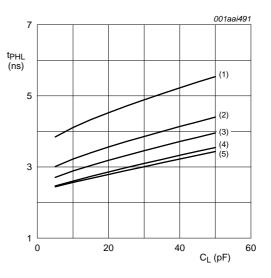


a. LOW to HIGH propagation delay (nAn to nBn); $V_{CC(A)} = 1.2 \text{ V}$

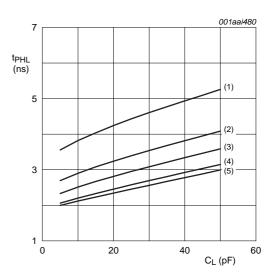


- c. LOW to HIGH propagation delay (nAn to nBn); $V_{CC(A)} = 1.5 \text{ V}$
- (1) $V_{CC(B)} = 1.2$ V.
- (2) V_{CC(B)} = 1.5 V.
- (3) V_{CC(B)} = 1.8 V.
- (4) $V_{CC(B)} = 2.5 V.$
- (5) V_{CC(B)} = 3.3 V.

Fig 10. Typical propagation delay versus load capacitance; T_{amb} = 25 °C



b. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 1.2 \text{ V}$

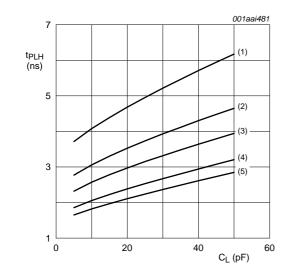


d. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 1.5 \text{ V}$

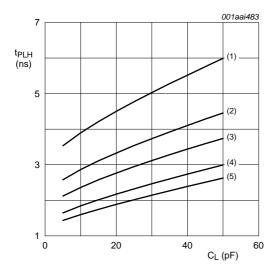
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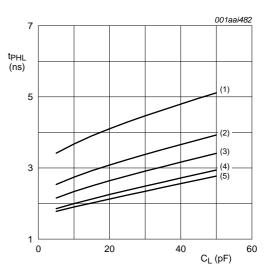


a. LOW to HIGH propagation delay (nAn to nBn); $V_{CC(A)}$ = 1.8 V

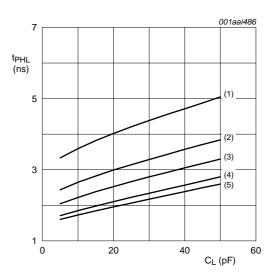


- c. LOW to HIGH propagation delay (nAn to nBn); $V_{CC(A)}$ = 2.5 V
- (1) $V_{CC(B)} = 1.2$ V.
- (2) V_{CC(B)} = 1.5 V.
- (3) V_{CC(B)} = 1.8 V.
- (4) $V_{CC(B)} = 2.5 V.$
- (5) V_{CC(B)} = 3.3 V.

Fig 11. Typical propagation delay versus load capacitance; $T_{amb} = 25 \text{ °C}$



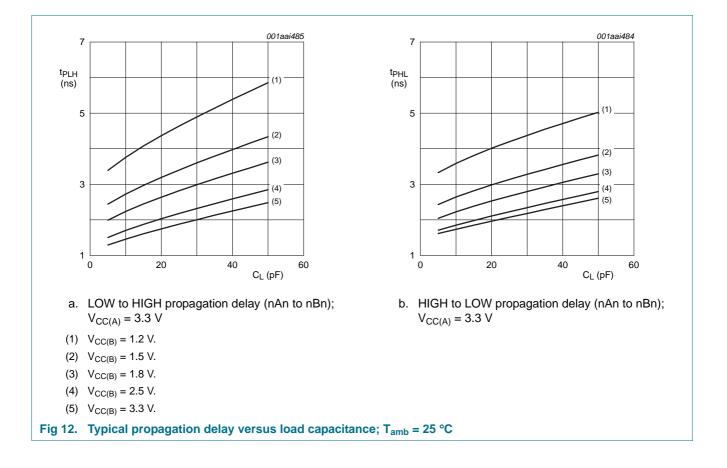
b. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 1.8 \text{ V}$



d. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 2.5 \text{ V}$

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13. Package outline

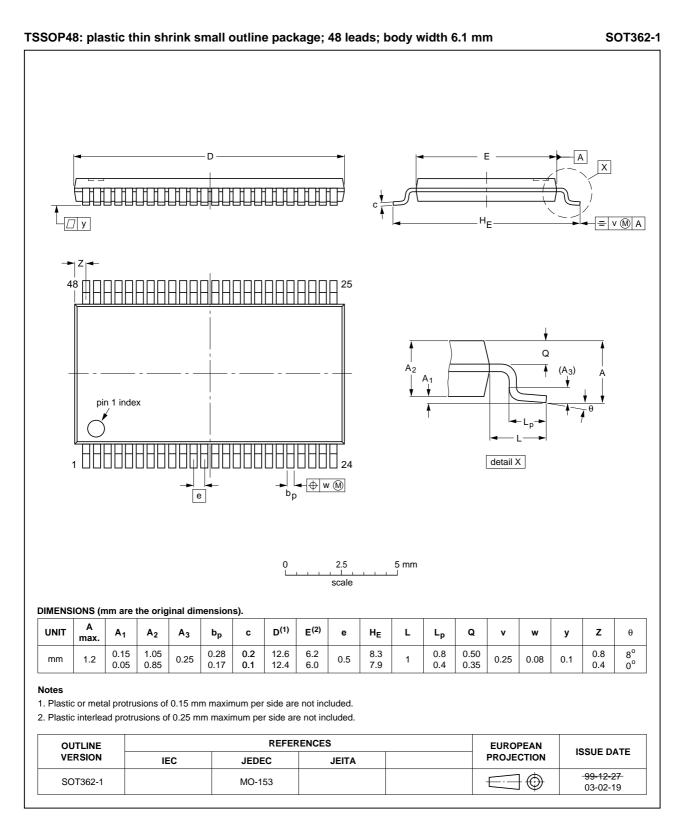
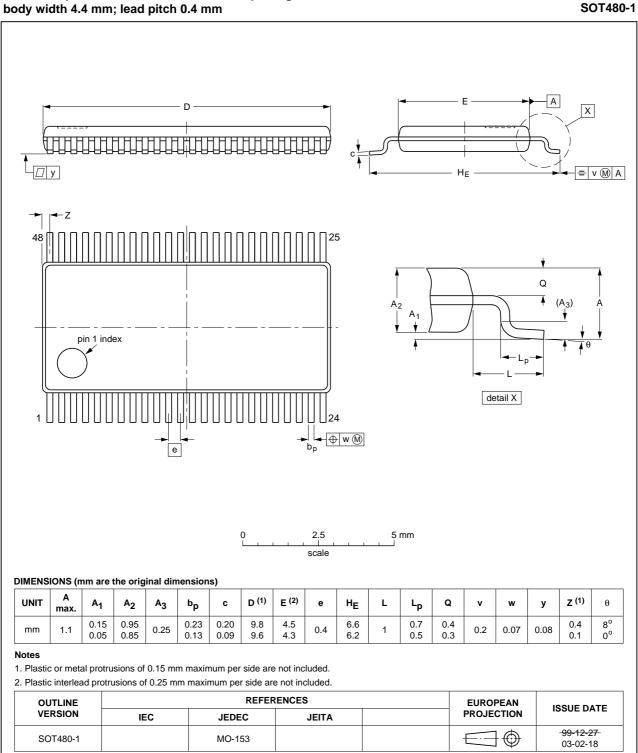


Fig 13. Package outline SOT362-1 (TSSOP48)

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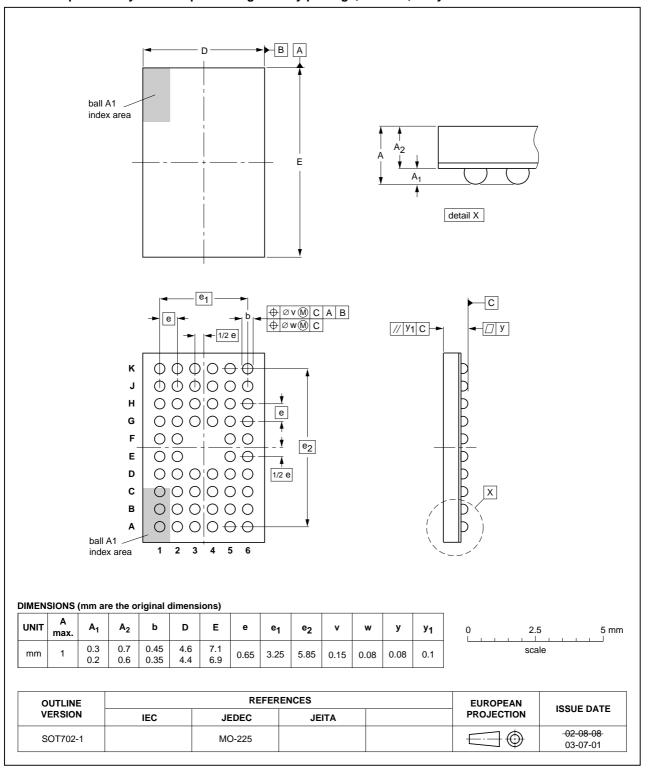


TSSOP48: plastic thin shrink small outline package; 48 leads; body width 4.4 mm; lead pitch 0.4 mm

Fig 14. Package outline SOT480-1 (TSSOP48)

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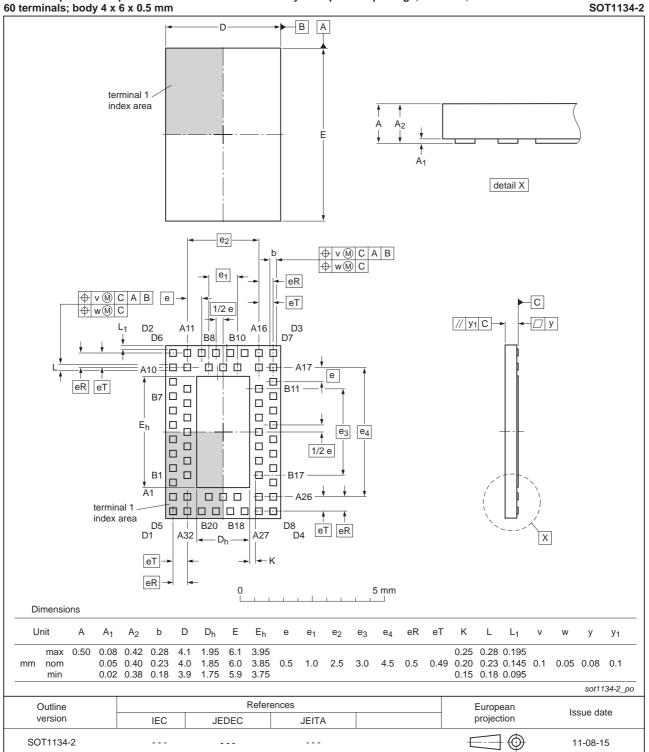




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Fig 15. Package outline SOT702-1 (VFBGA56)

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HXQFN60: plastic compatible thermal enhanced extremely thin quad flat package; no leads; 60 terminals; body 4 x 6 x 0.5 mm

Fig 16. Package outline SOT1134-2 (HXQFN60)

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14. Abbreviations

AcronymDescriptionCDMCharged Device ModelDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body Model	Table 16.	Abbreviations
DUTDevice Under TestESDElectroStatic DischargeHBMHuman Body Model	Acronym	Description
ESDElectroStatic DischargeHBMHuman Body Model	CDM	Charged Device Model
HBM Human Body Model	DUT	Device Under Test
	ESD	ElectroStatic Discharge
	HBM	Human Body Model
MM Machine Model	MM	Machine Model

15. Revision history

Table 17. Revision history

	-			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AVCH16T245 v.5	20120301	Product data sheet	-	74AVCH16T245 v.4
Modifications:	 For type nu 	mber 74AVCH16T245BX th	ne SOT code has change	ed to SOT1134-2.
74AVCH16T245 v.4	20111207	Product data sheet	-	74AVCH16T245 v.3
Modifications:	 Legal pages 	s updated.		
74AVCH16T245 v.3	20110616	Product data sheet	-	74AVCH16T245 v.2
74AVCH16T245 v.2	20100329	Product data sheet	-	74AVCH16T245 v.1
74AVCH16T245 v.1	20091014	Product data sheet	-	-

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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